

FLASH - SSD

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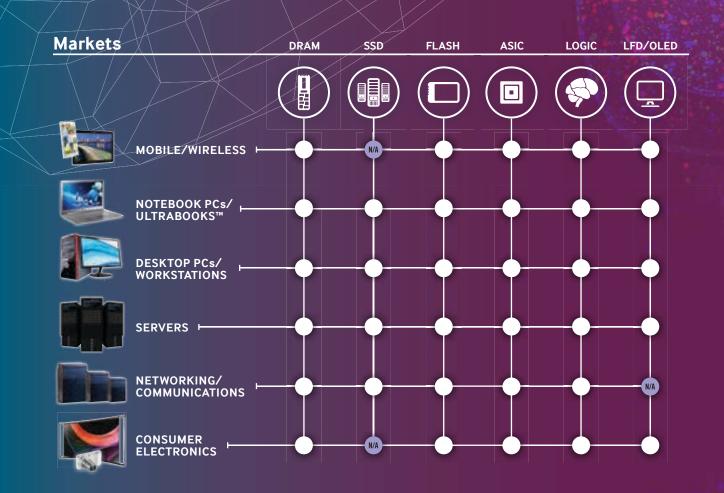




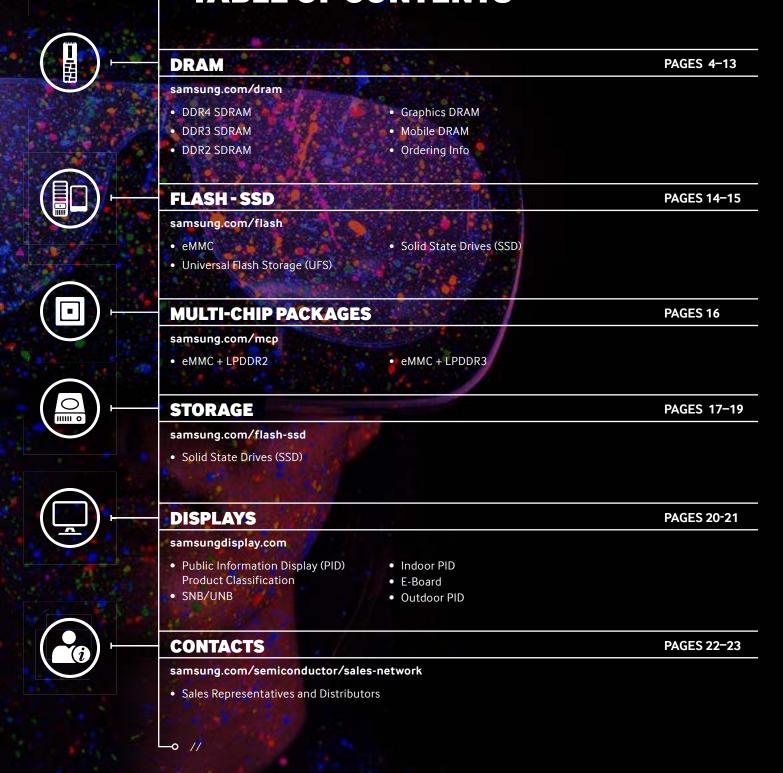
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## Samsung Semiconductor, Inc.

Samsung continues to lead the industry with the broadest portfolio of memory products and display technology. Its DRAM, flash, mobile and graphics memory are found in many computers — from ultrabooks to powerful servers — and in a wide range of handheld devices such as smartphones and tablets. Samsung is also a leader in display panels for smartphones, TVs and monitors and public information displays. In addition, Samsung provides the industry's widest line of storage products from the consumer to enterprise levels. These include optical disc drives as well as flash storage, such as Solid State Drives, and a range of embedded flash storage products.



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## **DDR4 SDRAM COMPONENTS**

Density	Voltage	Organization	Part Number	# Pins-Package	Compliance	Speed (Mbps)	Dimensions	Production
		1G x 4	K4A4G045WD-BCRC/PB	78 Ball -FBGA			7.5x11mm	
		512M x 8	K4A4G085WD-BCRC/PB	70 Dall -FDUA			7.3XTTIIIII	
4Gb	1.2V	256M x 16	K4A4G165WD-BCRC/PB	96 Ball -FBGA	Lead Free & Halogen Free, Flip Chip	2400/2133	7.5x13.3mm	Now
	1G x 4	K4A4G045WE-BCRC/PB	78 Ball -FBGA	Lead Free & Halogeri Free, Filp Chip	2400/2133	7.5x11mm	INOW	
		512M x 8	K4A4G085WE-BCRC/PB	70 Dall -I DUA			7.381111111	
		256M x 16	K4A4G165WE-BCRC/PB	96 Ball -FBGA			7.5x13.3mm	
8Gb	1 0\/	1G x 8	K4A8G085WB-BCRC/PB	78 Ball FBGA	Lead Free & Halogen Free, Flip Chip	2400/2133	7.5x11mm	Now
OGD	1.2V	512M x16	K4A8G165WB-BCRC/PB	96 Ball -FBGA	Lead Free & Halogeri Free, Filp Chip	2400/2133	7.5x13.3mm	INOW
16Gb	. 1.2V	2Gx8	K4AAG085WB-MCPB/RC	78 Ball -FBGA	Lead Free & Halogen Free, Flip Chip	2133/2400	7.5x13.3mm	Now
(8Gb DDP)	1.27	2010	K4AAG165WB-MCPB/RC	70 Dall -I DUA	Lead Free & Hallogeri Free, Filip Critip	2133/2400	1.0.13.311111	INOW

## **DDR4 SDRAM REGISTERED MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production	
4GB	1.2V	1G x 72	M393A5143DB0-CPB	4Ch /E10M v0\ * 0	Lond From 9 Hologon From Flin Chin	2133	4	Now	
4GB	1.2V	16 X / 2	M393A5143DB0-CRC	4Gb (512M x8) * 9	Lead Free & Halogen Free, Flip Chip	2400		INOW	
			M393A1G40DB0-CPB	40h /10 (\ \ 10		2133	4		
			M393A1G40DB1-CRC	4Gb (1G x4) * 18		2400		Now  Now  Now  Now  Now  Now  Now	
			M393A1G43DB0-CPB	40h /F10M v0\ * 10		2133	0		
)OD	1.01/	10 70	M393A1G43DB1-CRC	4Gb (512M x8) * 18	Lood From 9 Holonon From Flin Chin	2400	2		
3GB	1.2V	1G x 72	M393A1G40EB1-CPB	40h /10 (\ \ 10	Lead Free & Halogen Free, Flip Chip	2133	4	INOW	
			M393A1G40EB1-CRC	4Gb (1G x4) * 18		2400			
			M393A1G43EB1-CPB	40h /F10M v0\ * 10		2133	0		
			M393A1G43EB1-CRC	4Gb (512M x8) * 18		2400	2		
			M393A2G40DB0-CPB			2133	2 2 1 2 2		
16GB 1.2V			M393A2G40DB1-CRC	40h (40 4) * 00		2400			
			M393A2G40EB1-CPB	4Gb (1G x4) * 36		2133	2		
	1.2V	2G x 72	M393A2G40EB1-CRC		Lead Free & Halogen Free, Flip Chip	2400		Now Now Now	
			M393A2K40BB0-CPB	0.01- (0.04) * 4.0		2133	1		
			M393A2K40BB1-CRC	8Gb (2G x4) * 18		2400			
			M393A2K43BB1-CPB/CRC	8Gb (1G x8) * 18		2133/2400	2		
100D	1.2V	40 70	M393A4K40BB0-CPB	006 (004) * 00	Lood Free & Helegen Free Flin Chin	2133	0	Name	
32GB	1.2V	4G x 72	M393A4K40BB1-CRC	8Gb (2G x4) * 36	Lead Free & Halogen Free, Flip Chip	2400	2	INOW	
			M393A8G40D40-CRB	4Gb 4H TSV (4G x4) * 36	Lead Free & Halogen Free, 4High TSV	2133	8		
34GB TSV	1.2V	8G x 72	M393A8K40B21-CRB	0.0h 0.1.T0.1/4.04) * 0.0	Lood From 9 Holoson From Ollinh TCV	2133	4	Now	
	1.2v 00 x		M393A8K40B21-CTC	8Gb 2H TSV (4G x4) * 36	Lead Free & Halogen Free, 2High TSV	2400	4		
128GB FSV	1.2V	16G x 72	M393AAK40B41-CTC	8Gb 4H TSV (8G x4) * 36	Lead Free & Halogen Free, 4High TSV	2400	8	Now	
lotes:	DDR4 4Gb			= Inphi PB = DDR4-2133(15					
	DDR4 4Gb	(E die) based 0	· ·	RC = DDR4-2400(17 = Inphi PB = DDR4-2133(15 = Inphi RC = DDR4-2400(17	5-15-15)				
DDR4 (B Die) 8Gb based			= IDT	PB = DDR4-2133(15					

## **DDR4 SDRAM Load Reduced REGISTERED MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
			M386A4G40DM0-CPB	40h DDD (00 v4) * 00	Lead Free & Halogen Free, DDP	2133	1	
32GB	32GB 1.2V 4G x 72	4G x 72	M386A4G40DM1-CRC	4Gb DDP (2G x4) * 36	Lead Free & Haloger Free, DDI	2400	4	Now
			M386A4K40BB0-CRC5	8G (2Gx4)*36	(2Gx4)*36 Lead Free & Halogen Free, Flip Ch		2	
64GB	1.2V	8G x 72	M386A8K40BM1-CPB/CRC	8Gb DDP (4G x4) * 36	Lead Free & Halogen Free, DDP	2133/2400	4	Now
128GB	1.2V	16G x 72	M386AAK40B40-CUC	8Gb 4H TSV (8G x4) * 36	Lead Free & Halogen Free, DDP	2400	8	Now
Notes:		e) 8Gb based	5 = IDT $4 = Montage$ RC $0 = IDT$ $4 = Montage$ PB	= DDR4-2133(15-15-15) = DDR4-2400(17-17-17) = DDR4-2133(15-15-15) = DDR4-2400(17-17-17)				

## **DDR4 SDRAM VLP REGISTERED MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
16GB 1.2V	1 01/	2G x 72	M392A4K40BM0-CPB/RC	4Gb DDP (2G x4) * 18	Lead Free & Halogen Free, DDP	2133	2	Now
TOGD	16GB 1.2V 2G x 7	20 X / Z	M392A2K43BB0-CPB/RC	8Gb (1G x8) * 18	Lead Free & Halogen Free, Flip Chip	2133/2400	2	INOW
32GB	1.2V	4G x 72	M392A4K40BM0-CPB/RC	8Gb DDP (4G x4) * 18	Lead Free & Halogen Free, DDP	2133/2400	2	Now

## **DDR4 SDRAM UNBUFFERED MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
			M378A5143DB0-CPB			2133		
			M378A5143EB1-CPB	4Gb (512M x8) *8		2133		Now Now
4GB	1.2V	512M x 64	M378A5143EB2-CRC		Lead Free & Halogen Free	2400	1	
			M378A5244CB0-CPB			2133		
			M378A5244CB0-CRC			2400		
			M378A1G43DB0-CPB	40b (F10M v0) *10		2133		
202		10 04	M378A1G43EB1-CRC	4Gb (512M x8) *16		2400		Now
	1.01/	1G x 64	M378A1K43BB1-CPB		Lood Free 9 Helenen Free	2133	2	
8GB	1.2V		M378A1K43BB2-CRC	00b (100) *0	Lead Free & Halogen Free	2400		
		1D 0	M378A1K43CB2-CPB	8Gb (1G x8) *8		2133	4	
		1R x 8	M378A1K43CB2-CRC				- 1	
			M378A2K43BB1-CPB			2133		
100D	1.01/	00 04	M378A2K43BB1-CRC	006 (100) * 10	Lond Fran O Halaman Fran	2400		New
16GB 1	1.2V	2G x 64	M378A2K43CB1-CPB	8Gb (1G x8) * 16	Lead Free & Halogen Free	2133	2	NOW
			M378A2K43CB1-CRC			2400		

Notes: PB = DDR4-2133(15-15-15) RC = DD R4-2400(17-17-17)

#### **DDR4 SDRAM ECC UNBUFFERED MODULES**

RC = DDR4-2400(17-17-17)

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
4GB	1.2V	512M x72	M391A5143EB1-CPB/CRC	M391A5143EB1-CPB/CRC	Lead Free & Halogen Free, Flip Chip	2133/2400	1	Now
000 4.01/	1.01/	1070	M391A1G43DB0-CPB/CRC	M391A1G43DB0-CPB/CRC	Lood Free Ollelegen Free Film Ohio	0100/0400	0	New
8GB	3 1.2V 1G x72	M391A1K43BB1-CPB/CRC	M391A1K43BB1-CPB/CRC		2133/2400	2	Now	
16GB	1.2V	2G x72	M391A2K43BB1-CPB/CRC	M391A2K43BB1-CPB/CRC	Lead Free & Halogen Free, Flip Chip	2133/2400	2	Now

#### **DDR4 SDRAM SODIMM MODULES**

PB = DDR4-2133(15-15-15)

Notes:

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
			M471A5143DB0-CPB	4Gb (512M x8) * 8		2133	1	Now
4GB	1.2V	512M x 64	M471A5143EB0-CPB/RC	400 (312101.00) 0	Lead Free & Halogen Free	2133/2400		INOW
		M471A5244CB0-CPB/RC			2100/2400			
	8GB 1.2V 1G x 64	M471A1G43DB0-CPB	4Gb (512M x8) * 16		2133	2		
8GB		1G x 64	M471A1G43EB1-CPB/CRC	4db (312lvi xo) 10	Lead Free & Halogen Free		2	Now
OUD	1.20	10 x 04	M471A1K43BB1-CPB/CRC	8Gb (1Gx8)*8	Leau Fiee & Halogell Fiee	2133/2400	1	INOW
			M471A1K43CB1-CPB/CRC	odu (Taxo) o				
16CD	16GB 1.2V 2	2G x 64	M471A2K43BB1-CPB/RC	8Gb (1G x8) * 16	0.00 * 40	2133/2400	2	Now
TOUD		20 X 04	M471A2K43CB1-CPB/RC	odb (1d xo) 10	Lead Free & Halogen Free	2133/2400	2	INOW

Notes: PB = DDR4-2133(15-15-15) RC = DDR4-2400(17-17-17)

## **DDR4 SDRAM ECC SODIMM MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
		M474A1G43DB0-CPB			2133			
8GB	8GB 1.2V 1G x 72	1G x 72	M474A1G43DB1-CRC	4Gb (512M x8) * 18	Lead Free & Halogen Free, Flip Chip	2400	2	Now
			M474A1G43EB1-CPB/CRC	-		2133/2400		
16GB	1.2V	2G x 72	M474A2K43BB1-CPB/RC	8Gb (1G x8) * 18	Lead Free & Halogen Free, Flip Chip	2133/2400	2	Now

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## **DDR3 SDRAM REGISTERED MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
	1.5V		M393B1G70EB0-CMA	4Gb (1G x4) * 18		1866	1	
8GB	1.00	1G x 72	M393B1G73EB0-CMA	4Gb (512M x8) * 18	Lond From 9 Hologop From Flip Chip	1000	2	Now
OUD	1.35V	10 x 72	M393B1G70EB0-YK0	4Gb (1G x4) * 18	Lead Free & Halogen Free, Flip Chip	1600	1	INOW
	1.557		M393B1G73EB0-YK0	4Gb (2R x8) * 18		1000	2	
	1.5V		M393B2G70DB0-CMA			1866		
16GB	VG.1	2G x 72	M393B2G70EB0-CMA	4Gb (1G x4) * 36	Lond From 9 Hologop From Flip Chip	1000	2	Now
TOGB	1.051/	20 X / Z	M393B2G70DB0-YK0	4GD (1G X4) 30	Lead Free & Halogen Free, Flip Chip	1600	2	INOW
	1.35V		M393B2G70EB0-YK0			1600		
32GB	1.35V	4G x 72	M393B4G70DM0-YH9	4Gb DDP (2G x4) * 36	Lead Free & Halogen Free. DDP	1333	4	Now
Notes:	8 = IDT A1 9 = Inphi U		2 = IDT (E-die) 3 = Inphi (E-die)	YK = DDR3-1600 (11-11-11) MA = DDR3-1866 (13-13-13	,			

## **DDR3 SDRAM Load Reduced REGISTERED MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
32GB	1.35V	4G x 72	M386B4G70DM0-YK0	4Gb DDP (2G x4) * 36	Lead Free & Halogen Free, DDP	1600	4	Now
CACD	1.35V	00 70	M386B8G70DE0-YH9(4)	40h 000 (40 v.4) * 00	Lood Free 9 Helegen Free ODD	1333	0	New
64GB	1.5V	8G x 72	M386B8G70DE0-CK0(4)	4Gb QDP (4G x4) * 36	Lead Free & Halogen Free, QDP	1600	ŏ	Now

Notes: 3 = Inphi iMB GS02B 4 = Montage C1

#### **DDR3 SDRAM VLP REGISTERED MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
	1.5V		M392B1G70DB0-CMA	4Gb (1Gx4) * 18		1866	1	
8GB	1.50	1G x 72	M392B1G73DB0-CMA	4Gb (512M x8) * 18	Lead Free & Halogen Free, Flip Chip	1000	2	Now
OUD	8GB 1.35V	10 X / Z	M392B1G70DB0-YK0	4Gb (1Gx4) * 18	Lead Free & Halogen Free, Filip Grilp	1600	1	INOW
	1.557	.V	M392B1G73DB0-YK0	4Gb (512M x8) * 18		1000	2	
16GB	1.5V	2C v 72	M392B2G70DM0-CMA	4Gb DDP (2G x4) * 18	Lead Free & Halogen Free, DDP	1866	2	Now
TOUD	1.35V 2G x 72	20 X / Z	M392B2G70DM0-YK0	400 DDF (20 X4) 10	Leau Flee & Halogell Flee, DDF	1600	2	INOW
32GB	1.35V	4G x 72	M392B4G70DE0-YH9	4Gb QDP (4G x4) * 18	Lead Free & Halogen Free, QDP	1333	4	Now

Notes: 2 = IDT 3 = Inphi YK = DDR3-1600 MA = DDR3-1866 (13-13-13)

## **DDR3 Non ECC UNBUFFERED MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
			M378B5173DB0-CK0/CMA					
4GB	4GB 1.5V	512M x 64	M378B5173EB0-CK0/CMA	4Gb (512M x8) * 8	Lead Free & Halogen Free. Flip Chip	1600/1866	1	Now
			M378B5173EB0-YK0/*CMA	_				
	1 5\/		M378B1G73DB0-CK0/MA					
8GB	1.5V		M378B1G73EB0-CK0/CMA	4Gb (512M x8) * 16	Lead Free & Halogen Free. Flip Chip	1600/1866	2	Now
	1.35V		M378B1G73EB0-YK0/*CMA					

Notes: YK = DDR3-1600 (11-11-11) MA = DDR3-1866 (13-13-13) \* 1.35V is compatible to 1.5V

#### DDR3 SDRAM UNBUFFERED MODULES (ECC)

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
4CD	1.5V	512Mx72	M391B5173EB0-CMA	40b (E10M v0) * 0	Lond From 9 Hologop From	1866	4	Now
4GB	1.35V	31ZIVIX/Z	M391B5173EB0-YK0	4Gb (512M x8) * 9 Lead Free & Halogen Free		1600		Now
OCD	1.5V	1G x 72	M391B1G73EB0-CMA	40b (E10M v0) * 10	Lond From 9 Hologon From	1866	0	Now
8GB	1.35V	16 X 7 Z	M391B1G73EB0-YK0	4Gb (512M x8) * 18	Lead Free & Halogen Free	1600	2	Now

Notes: YK0 = DDR3-1600 (11-11-11) MA = DDR3-1866 (13-13-13)

## **DDR3 SDRAM SODIMM MODULES**

Density	Voltage	Organization	Part Number	Composition	Compliance	Speed (Mbps)	Ranks	Production
4GB	1.35V	512M x 72	M474B5173EB0-YK0	4Gb (512M x8) * 9	Lead Free & Halogen Free, Flip Chip	1866	1	Now
000	1.5V	10 70	M474B1G73EB0-CMA	40h (F10M v0) * 10	Lood Free 9 Holosop Free File Chie	1866	0	Now
8GB	1.35V	1G x 72	M474B1G73EB0-YK000	4Gb (512M x8) * 18	Lead Free & Halogen Free, Flip Chip	1600		Now

## **DDR3 SDRAM COMPONENTS**

Density	Voltage	Organization	Part Number	# Pins- Package	Compliance	Speed (Mbps)	Dimensions	Production
	1.5V	128M x 8	K4B1G0846I-BCK0/MA/NB	78 Ball -FBGA		1600/1866/2133	7.5x11mm	
1Gb	1.3V	128M x 16	K4B1G1646I-BCK0/MA/NB	96 Ball -FBGA	Lead Free & Halogen Free, Flip Chip	1000/1000/2133	7.5x13.3mm	Now
TGD	1.35V	128M x 8	K4B1G0846I-BYK0/MA	78 Ball -FBGA	Leau Free & Halogeri Free, Filp Grilp	1600/1800	7.5x11mm	INOW
	1.33V	128M x 16	K4B1G1646I-BYK0/MA	96 Ball -FBGA		1000/1000	7.5x13.3mm	
	1 5\/	512M x 8	K4B2G0846F-BCK0/MA/NB	78 Ball -FBGA		1600/1066/0100	7.5x11mm	
OCh.	1.5V	256M x 16	K4B2G1646F-BCK0/MA/NB	96 Ball -FBGA	Lond Frag & Halagan Frag Flin Chin	1600/1866/2133	7.5x13.3mm	Now
2Gb	1.051/	256M x 8	K4B2G0846F-BK0/MA	78 Ball -FBGA	Lead Free & Halogen Free, Flip Chip	1600/1066	7.5x11mm	INOW
	1.35V	128M x 16	K4B2G1646F-BK0/MA	96 Ball -FBGA		1600/1866	7.5x13.3mm	
	512M x 8	K4B4G0846D-BCK0/MA/NB	78 Ball -FBGA			7.5x11mm		
	1.577	256M x 16	K4B4G1646D-BCK0/MA/NB	96 Ball -FBGA	Lead Free & Halogen Free, Flip Chip	1600/1866/2133	7.5x13.3mm	Now
	1.5V	512M x 8	K4B4G0846E-BCK0/MA/NB	78 Ball -FBGA	Lead Free & Halogen Free, Filp Grilp		7.5x11mm	
		256M x 16	K4B4G1646E-BCK0/MA/NB	96 Ball -FBGA			7.5x13.3mm	
10h		1G x 4	K4B4G0446D-BYK0	70 Dall EDGA		1000	7.5x11mm	
4Gb		512M x 8	K4B4G0846D-BYK0	78 Ball -FBGA		1600	7.5x11mm	
	4.057	256M x 16	K4B4G1646D-BYK0/MA	96 Ball -FBGA	Land France Oldstannan France Film Obin		7.5x13.3mm	Name
	1.35V	1G x 4	K4B4G0446E-BYK0/MA	70 D-II FD0A	Lead Free & Halogen Free, Flip Chip	1000/1000	7.5x11mm	Now
		512M x 8	K4B4G0846E-BYK0/MA	78 Ball -FBGA		1600/1866	7.5x11mm	
		256M x 16	K4B4G1646E-BYK0/MA	96 Ball -FBGA			7.5x13.3mm	
	4.577	E40M40	K4B8G1646Q-MCK0/MA					
006	1.5V 512M x 16 Gb 1.35V 512M x 16	512W1X 16	K4G8G1646D-MCK0/MA	OC Dell FDCA	Lood Free O. Helenen Free	1000/1000	11,100,000	New
8Gb		E40M 40	K4G8G1646D-MCK0/MA	96 Ball -FBGA	Lead Free & Halogen Free	1600/1866	11x13.3mm No	Now
		512M x 16	K4G8G1646D-MYK0/ (MA)					
Notes:		512M x 16		MA = DDR3-1866 (1	3-13-13) NB = DDB3-2133 (14-14-	14)		

Notes: H9 = DDR3-1333 (9-9-9) K0 = DDR3-1600 (11-11-11) MA = DDR3-1866 (13-13-13) NB = DDR3-2133 (14-14-14)

## **DDR2 SDRAM COMPONENTS**

Density	Organization	Part Number	# Pins-Package	Dimensions	Package	Speed (Mbps)	Production
512Mb	64M x 8	K4T51083QN-BCE7	60-FBGA	7.5x9.5mm	Lead free & Halogen free , Flip chip	667/800/1066	Now
SIZIVID	32M x 16	K4T51163QN-BCE7	84-FBGA	7.5x12.5mm	Lead free & Haloger free , Flip Chip	007/000/1000	INOW
10h	128M x 8	K4T1G084QJ-BCE7	60-FBGA	7.5x9.5mm	Load from 9 Hologon from Elin ohin	667/800/1066	Now
1Gb	64M x 16	K4T1G164QJ-BCE7	84-FBGA	7.5x12.5mm	Lead free & Halogen free , Flip chip	007/000/1000	INOW
Notes:	E6 = DDR2-667 (5	-5-5) E7 = DDR2-800 (5-5-5)	F7 = DDR2-800 (6-6-6	6) F8 = DDR2-1	066 (7-7-7)		

E6 = DDR2-667 (5-5-5) E7 = DDR2-800 (5-5-5) F7 = DDR2-800 (6-6-6) F8 = DDR2-1066 (7-7-7)

## **GRAPHICS DRAM COMPONENTS**

Туре	Density	Organization	Part Number	Package	VDD/VDDQ	Speed Bin (MHz)	Production
	8Gb 256M x 32	K4G80325FB-HC(03/28/25/22)		1.5V/1.5V	6000/7000/8000*/9000*		
GDDR5	odu	200WI X 32	K4G80325FB-HC(03/28/25/22)	170-FCFBGA	1.35V/1.35V	5000/6000/6500/TBD	Now
GDDRO	4Gb	128M x 32	K4G41325FE-HC2(03/28/25/22)	170-FUFDGA	1.5V/1.5V	6000/7000/8000*/9000*	Now
	460	128IVI X 32	K4G41325FE-HC2(03/28/25/22)		1.35V/1.35V	5000/6000/6500/TBD	
~DDD2	1Ch	OFCM v 16	K4W4G1646E-BC(1A/1B)	96-FCFBGA	1.5V/1.5V	2133/2400	Now
gDDR3	4Gb	256M x 16	K4W4G1646E-BC(1A/1B)	90-гоград	1.35V/1.35V	1866/2133	Now

Notes:

Package & Speed Bin Codes

H: FBGA (Halogen Free & Lead Free) (DDR3)
B: FCFBGA (Halogen Free & Lead Free) (DDR3)
H: FCFBGA (Halogen Free & Lead Free) (GDDR5)
F: FBGA (Halogen Free & Lead Free) (GDDR5)
22: 0.22ns (9000Mbps)

25: 0.25ns (8000Mbps)

28: 0.28ns (7000Mbps) 03: 0.3ns (6000Mbps) 04: 0.4ns (5000Mbps) 1B: 8.3ns (2400Mbps gDDR3) 1A: 1.0ns (2133Mbps gDDR3) 11: 1.1ns (1866Mbps)

## **MOBILE DRAM COMPONENTS**

Туре	Density	Organization	Part Number	Package	Power	Production
	8Gb	1011,400	K4E8E324EB-EGCF	178-FBGA, 11x11.5, SDP, 1866Mbps		
	800	1CH x 32	K4E8E324EB-AGCF	168-FBGA, 12x12, SDP, 1866Mbps		
	12Gb	1CH x32	K4E2E304EA-AGCF	168-FBGA, 12x12, DDP, 1866Mbps		
		1011 v 20	K4E6E304EB-EGCF 178-FBGA, 11x11.5, DDP, 1866Mbps			
	16Gb	1CH x 32	K4E6E304EB-AGCF	168-FBGA, 12x12, DDP, 1866Mbps		
LPDDR3	TOGU	2CH x 32	K3QF2F20BM-AGCF	253-FBGA, 11x11.5, DDP, 1866Mbps	1.8V/1.2V/1.2V	Now
LPDDRS		20H X 32	K3QF3F30BM-FGCF	256-FBGA, 14x14, DDP, 1866Mbps	1.0V/1.2V/1.2V	INOW
	24Gb	1CH x32	K4EHE304EA-AGCF	168-FBGA, 12x12, QDP, 1866Mbps		
	2400	2CH x32	K3QF6F60AM-FGCF	256-FBGA, 14x14, QDP, 1866Mbps		
		1CH x32	K4EBE304EB-EGCF	178-FBGA, 11x11.5, QDP, 1866Mbps		
	32Gb	2CH x32	K3QF4F40BM-AGCF	253-FBGA, 11x11.5, QDP, 1866Mbps		
		20H X32	K3QF4F40BM-FGCF	256-FBGA, 14x14, QDP, 1866Mbps		
	8Gb		K4F8E304HB-MGCJ	200-FBGA, 10x15, SDP, 3733Mbps		
	16Gb	2CH x16	K4F6E304HB-MGCJ	200-FBGA, 10x15, DDP, 3733Mbps		Now
	0.40h	200 810	K4FHE3D4HM-MFCJ	200-FBGA, 10x15, DDP, 3733Mbps		Now
LPDDR4	24Gb		K3RG4G40MM-MGCJ	366-FBGA, 15x15, DDP, 3733Mbps	1.8V/1.1V/1.1V	
	2006	401110	K3RG2G20CA-MGCJ	366-FBGA, 15x15, QDP, 3733Mbps		CS
	32Gb	4CH x16	K3RG2G20CM-FGCJ	432-FBGA, 15x15, QDP, 3733Mbps		ES
	48Gb	4CH x16	K3RG6G60MM-MGCJ	366-FBGA, 15x15, QDP, 3733Mbps		Now
I DDDD 4V	32Gb	401110	K3UH5H50MM-NGCJ	366-FBGA, 12x12.7 DDP, 3733Mbps	1 0//1 1//1 1//	00
LPDDK4X	DDR4X 32Gb 48Gb	4CH x16	K3UH6H60AM-NGCJ	366-FBGA, 12x12.7 QDP, 3733Mbps	1.8V/1.1V/1.1V	CS

#### COMPONENT DRAM ORDERING INFORMATION

	1	2	3	4	5	6	7	8	9	10	11	
	K	4	T	XX	XX	X	Х	Х	Х	Х	XX	
SAMSUNG Memory												Speed
DRAM												Temp & Powe
DRAM Type												Package Type
Density												Generation
												rface (VDD, VDDQ
Bit Organization											Numbe	r of Internal Bank

#### 1. Memory (K)

#### 2. DRAM: 4

## 3. DRAM Type

- B: DDR3 SDRAM
- D: GDDR SDRAM
- G: GDDR5 SDRAM
- H: DDR SDRAM
- J: GDDR3 SDRAM
- M: Mobile SDRAM
- N: SDDR2 SDRAM
- S: SDRAM
- T: DDR SDRAM
- U: GDDR4 SDRAM
- V: Mobile DDR SDRAM Power Efficient Address
- W: SDDR3 SDRAM
- X: Mobile DDR SDRAM
- Y: XDR DRAM
- Z: Value Added DRAM

## 4. Density

- 10: 1G, 8K/32ms
- 16: 16M, 4K/64ms
- 26: 128M, 4K/32ms
- 28: 128M, 4K/64ms
- 32: 32M, 2K/32ms
- 50: 512M, 32K/16ms
- 51: 512M, 8K/64ms
- 52: 512M, 8K/32ms
- 54: 256M, 16K/16ms
- 55: 256M, 4K/32ms
- 56: 256M, 8K/64ms
- 62: 64M, 2K/16ms
- 64: 64M, 4K/64ms
- 68: 768M, 8K/64ms 1G: 1G, 8K/64ms
- 2G: 2G, 8K/64ms
- 4G: 4G, 8K/64ms

#### 5. Bit Organization

- 02: x 2
- 04: x 4
- 06: x 4 Stack (Flexframe)
- 07: x 8 Stack (Flexframe)

- 08: x8
- 15: x 16 (2CS)
- 16: x 16
- 26: x 4 Stack (JEDEC Standard)
- 27: x 8 Stack (JEDEC Standard)
- 30: x 32 (2CS, 2CKE)
- 31: x 32 (2CS)
- 32: x 32

#### 6. # of Internal Banks

- 2: 2 Banks
- 3: 4 Banks
- 4: 8 Banks
- 5: 16 Banks

## 7. Interface (VDD, VDDQ)

- 2: LVTTL. 3.3V. 3.3V
- 4: LVTTL, 2.5V, 2.5V
- 5: SSTL-2 1.8V, 1.8V
- 6: SSTL-15 1.5V, 1.5V
- 8: SSTL-2, 2.5V, 2.5V
- A: SSTL, 2.5V, 1.8V
- F: POD-15 (1.5V, 1.5V)
- H: SSTL 2 DLL, 3.3V, 2.5V
- M: LVTTL, 1.8V, 1.5V
- N: LVTTL, 1.5V, 1.5V
- P: LVTTL, 1.8V, 1.8V
- Q: SSTL-2 1.8V. 1.8V
- R: SSTL-2, 2.8V, 2.8V
- U: DRSL, 1.8V, 1.2V

#### 8. Generation

- A: 2nd Generation
- B: 3rd Generation
- C: 4th Generation
- D: 5th Generation
- E: 6th Generation
- F: 7th Generation
- G: 8th Generation
- H: 9th Generation
- I: 10th Generation
- J: 11th Generation
- K: 12th Generation
- M: 1st Generation
- N: 14th Generation
- Q: 17th Generation

## 9. Package Type

#### **DDR2 DRAM**

- L: TSOP II (Lead-free & Halogen-free)
- H: FBGA (Lead-free & Halogen-free)
- F: FBGA for 64Mb DDR (Lead-free & Halogen-free)
- 6: sTSOP II (Lead-free & Halogen-free)
- T: TSOP II
- N: sTSOP II
- G: FBGA
- U: TSOP II (Lead-free)
- V: sTSOP II (Lead-free)
- Z: FBGA (Lead-free)

#### **DDR2 SDRAM**

- Z: FBGA (Lead-free)
- J: FBGA DDP (Lead-free)
- Q: FBGA QDP (Lead-free)
- H: FBGA (Lead-free & Halogen-free)
- M: FBGA DDP (Lead-free & Halogen-free)
- E: FBGA QDP (Lead-free & Halogen-free)
- T: FBGA DSP (Lead-free & Halogen-free, Thin)

#### **DDR3 SDRAM**

- Z: FBGA (Lead-free)
- H: FBGA (Halogen-free & Lead-free)

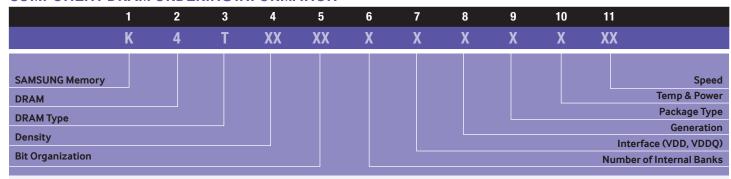
#### **Graphics Memory**

- Q: TQFP
- U: TQFP (Lead Free)
- G: 84/144 FBGA
- V: 144 FBGA (Lead Free)
- Z: 84 FBGA (Lead Free)
- T: TSOP
- L: TSOP (Lead Free)
- A: 136 FBGA
- B: 136 FBGA (Lead Free)
- H: FBGA (Hologen Free & Lead Free)
- E: 100 FBGA (Hologen Free & Lead Free)

#### **SDRAM**

- L TSOP II (Lead-free & Halogen-free)
- N: STSOP II
- T: TSOP II
- U: TSOP II (Lead-free)
- V: sTSOP II (Lead-free)

#### COMPONENT DRAM ORDERING INFORMATION



#### **XDR DRAM**

J: BOC(LF) P: BOC

#### **Mobile DRAM**

#### Leaded/Lead Free

G/A: 52balls FBGA Mono

R/B: 54balls FBGA Mono

X/Z: 54balls BOC Mono

J/V: 60(72)balls FBGA Mono 0.5pitch

L /F: 60balls FBGA Mono 0.8pitch

S/D: 90balls FBGA

#### Monolithic (11mm x 13mm)

F/H: Smaller 90balls FBGA Mono

Y/P: 54balls CSP DDP

M/E: 90balls FBGA DDP

# 10. Temp & Power - COMMON (Temp, Power)

C: Commercial, Normal (0'C – 95'C) & Normal Power

C: (Mobile Only) Commercial (-25  $\sim$  70'C), Normal Power

J: Commercial, Medium

L: Commercial, Low (0'C - 95'C) & Low Power

L: (Mobile Only) Commercial, Low, i-TCSR

F: Commercial, Low, i-TCSR & PASR & DS

E: Extended (-25~85'C), Normal

N: Extended, Low, i-TCSR

G: Extended, Low, i-TCSR & PASR & DS

I: Industrial, Normal (-40'C – 85'C) & Normal Power

P: Industrial, Low (-40'C - 85'C) & Low Power

H: Industrial, Low, i-TCSR & PASR & DS

## 11. Speed (Wafer/Chip Biz/BGD: 00)

#### **DDR SDRAM**

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CC: DDR400 (200MHz @ CL=3, tRCD=3, tRP=3)

B3: DDR333 (166MHz @ CL=2.5, tRCD=3, tRP=3) \*1

A2: DDR266 (133MHz @ CL=2 , tRCD=3, tRP=3)

B0: DDR266 (133MHz @ CL=2.5, tRCD=3,

Note 1: "B3" has compatibility with "A2" and "B0"

#### DDR2 SDRAM

CC: DDR2-400 (200MHz @ CL=3, tRCD=3, tRP=3)

D5: DDR2-533 (266MHz @ CL=4, tRCD=4, tRP=4)

E6: DDR2-667 (333MHz @ CL=5, tRCD=5, tRP=5)

F7: DDR2-800 (400MHz @ CL=6, tRCD=6, tRP=6)

E7: DDR2-800 (400MHz @ CL=5, tRCD=5, tRP=5)

#### **DDR3 SDRAM**

F7: DDR3-800 (400MHz @ CL=6, tRCD=6, tRP=6)

F8: DDR3-1066 (533MHz @ CL=7, tRCD=7, tRP=7)

G8: DDR3-1066 (533MHz @ CL=8, tRCD=8, tRP=8)

H9: DDR3-1333 (667MHz @ CL=9, tRCD=9, tRP=9)

K0: DDR3-1600 (800MHz @ CL=11, tRCD=11, tRP=11)

MA: DDR3-1866 (933MHz @ CL=13, tRCD=13, tRP=13)

NB: DDR3-2133 (1067MHz @ CL=14, tRCD=14, tRP=14)

#### **Graphics Memory**

18: 1.8ns (550MHz)

04: 0.4ns (2500MHz)

20: 2.0ns (500MHz)

05: 0.5ns (2000MHz)

22: 2.2ns (450MHz)

5C: 0.56ns (1800MHz)

25: 2.5ns (400MHz)

06: 0.62ns (1600MHz)

2C: 2.66ns (375MHz)

6A: 0.66ns (1500MHz)

2A: 2.86ns (350MHz)

07: 0.71ns (1400MHz)

33: 3.3ns (300MHz)

7A: 0.77ns (1300MHz)

36: 3.6ns (275MHz)

08: 0.8ns (1200MHz)

40: 4.0ns (250MHz)

09: 0.9ns (1100MHz)

45: 4.5ns (222MHz)

1:1.0ns (1000MHz)

50/5A: 5.0ns (200MHz)

1:1.1ns (900MHz)

55: 5.5ns (183MHz)

12: 1.25ns (800MHz)

60: 6.0ns (166MHz)

14: 1.4ns (700MHz)

16: 1.6ns (600MHz)

#### SDRAM (Default CL=3)

50: 5.0ns (200MHz CL=3)

60: 6.0ns (166MHz CL=3)

67: 6.7ns

75: 7.5ns PC133 (133MHz CL=3)

#### **XDR DRAM**

A2: 2.4Gbps, 36ns, 16Cycles

B3: 3.2Gbps, 35ns, 20Cycles

C3: 3.2Gbps, 35ns, 24Cycles

C4: 4.0Gbps, 28ns, 24Cycles

DS: Daisychain Sample

#### Mobile-SDRAM

60: 166MHz, CL 3

75: 133MHz, CL 3

80: 125MHz, CL 3

1H: 105MHz, CL 2

1L: 105MHz, CL 3

15: 66MHz, CL 2 & 3

#### Mobile-DDR

C3: 133MHz, CL 3

C2: 100MHz, CL 3

C0: 66MHz, CL 3

Note: All Lead-free and Halogen-free products are in compliance with RoHS

#### MODULE DRAM ORDERING INFORMATION

	1	2	3	4	5	6	7	8	9	10	11	12	13	
	M	Х	XX	T	XX	X	Х	X	Х	X	Х	XX	Х	
SAMSUNG Memory														AMB Vendor
DIMM														Speed
Data bits														Temp & Power
DRAM Component 1	Гуре													PCB Revision
Depth														Package
Number of Banks														Generation
Bit Organization														

## 1. Memory Module: M

## 2. DIMM Type

- 3: DIMM
- 4: SODIMM

#### 3. Data bits

- 12: x 72 184pin Low Profile Registered DIMM
- 63: x 63 PC100/PC133  $\mu$ SODIMM with SPD for 144pin
- 64: x 64 PC100/PC133 SODIMM with SPD for 144pin (Intel/JEDEC)
- 66: x 64 Unbuffered DIMM with SPD for 144pin/168pin (Intel/JEDEC)
- 68: x 64 184pin Unbuffered DIMM
- 70: x 64 200pin Unbuffered SODIMM
- 71: x 64 204pin Unbuffered SODIMM
- 74: x 72/ECC Unbuffered DIMM with SPD
  - for 168pin (Intel/JEDEC)
- 77: x 72/ECC PLL + Register DIMM with SPD for 168pin (Intel PC100)
- 78: x 64 240pin Unbuffered DIMM
- 81: x 72 184pin ECC unbuffered DIMM
- 83: x 72 184pin Registered DIMM
- 90: x 72/ECC PLL + Register DIMM
- 91: x 72 240pin ECC unbuffered DIMM
- 92: x 72 240pin VLP Registered DIMM
- 93: x 72 240pin Registered DIMM
- 95: x 72 240pin Fully Buffered DIMM with SPD for 168pin (JEDEC PC133)

#### 4. DRAM Component Type

- B: DDR3 SDRAM (1.5V VDD)
- L: DDR SDRAM (2.5V VDD)
- S: SDRAM
- T: DDR2 SDRAM (1.8V VDD)

#### 5. Depth

- 09: 8M (for 128Mb/512Mb)
- 17: 16M (for 128Mb/512Mb)
- 16: 16M
- 28: 128M
- 29: 128M (for 128Mb/512Mb)
- 32: 32M
- 33: 32M (for 128Mb/512Mb)
- 51: 512M
- 52: 512M (for 512Mb/2Gb)
- 56: 256M
- 57: 256M (for 512Mb/2Gb)
- 59: 256M (for 128Mb/512Mb)
- 64: 64M
- 65: 64M (for 128Mb/512Mb)
- 1G: 1G
- 1K: 1G (for 2Gb)

#### 6. # of Banks in Comp. & Interface

- 1: 4K/64mxRef., 4Banks & SSTL-2
- 2:8K/64ms Ref., 4Banks & SSTL-2
- 2: 4K/64ms Ref., 4Banks & LVTTL (SDR Only)
- 5: 8K/64ms Ref., 4Banks & LVTTL (SDR Only)
- 5: 4Banks & SSTL-1.8V
- 6: 8Banks & SSTL-1.8V

## 7. Bit Organization

- 0: x 4
- 3: x 8
- 4: x16
- 6: x 4 Stack (JEDEC Standard)
- 7: x 8 Stack (JEDEC Standard)
- 8: x 4 Stack
- 9: x 8 Stack

#### 8. Generation

- A: 2nd Gen.
- B: 3rd Gen.
- C: 4th Gen.
- D: 5th Gen.
- E: 6th Gen.
- F: 7th Gen.
- G: 8th Gen.
- M: 1st Gen.
- Q: 17th Gen.

## 9. Package

- E: FBGA QDP (Lead-free & Halogen-free)
- G: FBGA
- H: FBGA (Lead-free & Halogen-free)
- J: FBGA DDP (Lead-free)
- M: FBGA DDP (Lead-free & Halogen-free)
- N: sTSOP
- Q: FBGA QDP (Lead-free)
- T: TSOP II (400mil)
- U: TSOP II (Lead-Free)
- V: sTSOP II (Lead-Free)
- Z: FBGA (Lead-free)

#### 10. PCB Revision

- 0: Mother PCB
- 1: 1st Rev
- 2: 2nd Rev.
- 3: 3rd Rev.
- 4: 4th Rev.
- A: Parity DIMM
- S: Reduced PCB
- U: Low Profile DIMM

## 11. Temp & Power

- C: Commercial Temp. (0°C  $\sim$  95°C) & Normal Power
- L: Commercial Temp. (0°C ~ 95°C) & Low Power

#### 12. Speed

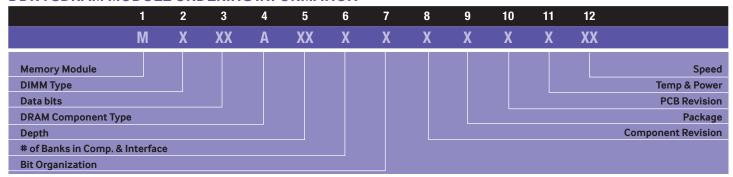
- CC: (200MHz @ CL=3, tRCD=3, tRP=3)
- D5: (266MHz @ CL=4, tRCD=4, tRP=4)
- E6: (333MHz @ CL=5, tRCD=5, tRP=5)
- F7: (400MHz @ CL=6, tRCD=6, tRP=6)
- E7: (400MHz @ CL=5, tRCD=5, tRP=5)
- F8: (533MHz @ CL=7, tRCD=7, tRP=7)
- G8: (533MHz @ CL=8, tRCD=8, tRP=8)
- H9: (667MHz @ CL=9, tRCD=9, tRP=9)
- K0: (800MHz @ CL=10, tRCD=10, tRP=10)
- 7A: (133MHz CL=3/PC100 CL2)

#### 13. AMB Vendor for FBDIMM

- 0, 5: Intel
- 1, 6, 8: IDT
- 9: Montage
- Note: All Lead-free and Halogen-free products are in compliance with RoHS

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### **DDR4 SDRAM MODULE ORDERING INFORMATION**



## 1. Memory Module: M

#### 2. DIMM Type

- 3: R/LRDIMM
- 4: SODIMM

#### 3. Data bits

- 74: x 72 260pin SODIMM
- 86: x 72 288pin Load Reduced DIMM
- 93: x 72 288pin Registered DIMM

#### 4. DRAM Component Type

A: DDR4 SDRAM (1.2V VDD)

#### 5. Depth

- 1G: 1G
- 2G: 2G
- 4G: 4G
- 8G: 8G
- 1K: 1G (for 8Gb)
- 2K: 2G (for 8Gb)

## 6. # of Banks in Comp. & Interface

4: 16Banks & POD-1.2V

## 7. Bit Organization

- 0: x 4
- 3: x 8

## 8. Component Revision

- M: 1st Gen.
- A: 2nd Gen.
- B: 3rd Gen.
- C: 4th Gen.
- D: 5th Gen.
- E: 6th Gen.
- F: 7th Gen.
- G: 8th Gen.

## 9. Package

B: FBGA (Halogen-free & Lead-free, Flip Chip) M: FBGA (Halogen-free & Lead-free, DDP)

#### 10.PCB Revision

- 0: None
- 1: 1st Rev.
- 2: 2nd Rev.
- 3: 3rd Rev.
- 4: 4th Rev.

## 11. Temp & Power

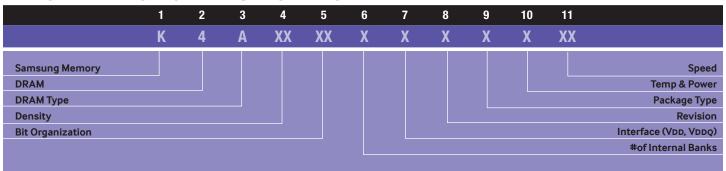
C: Commercial Temp. (0°C ~ 85°C) & Normal Power

#### 12.Speed

PB: DDR4-2133

(1066MHz @ CL=15, tRCD=15, tRP=15)

## **DDR4 SDRAM MEMORY ORDERING INFORMATION**



## 1. Samsung Memory: K

## 2. DRAM: 4

#### 3. DRAM Type

A: DDR4 SDRAM

## 4. Density

4G: 4Gb

8G: 8Gb

## 5. Bit Organization

04: x 4 08: x 8

#### 6. # of Internal Banks

5: 16Banks

## 7. Interface (VDD, VDDQ)

W: POD (1.2V, 1.2V)

#### 8. Revision

M: 1st Gen.

A: 2nd Gen.

B: 3rd Gen.

C: 4th Gen.

D: 5th Gen.

E: 6th Gen.

F: 7th Gen.

G: 8th Gen.

H: 9th Gen.

## 9. Package Type

B: FBGA (Halogen-free & Lead-free, Flip Chip)
M: FBGA (Halogen-free & Lead-free, DDP)

## 10. Temp & Power

C: Commercial Temp. (0°C  $\sim$  85°C) & Normal Power

#### 11.Speed

PB: DDR4-2133

(1066MHz @ CL=15, tRCD=15, tRP=15)

RC: DDR4-2400

(1200MHz @ CL=17, tRCD=17, tRP=17)

## **MOBILE STORAGE**

Application	Product	Density	Org	Туре	Flash Die	Part Number	Seq R/W MB/s	Random R/W IOPS	mm Pkg Size (X,Y,Z)	Status
	UFS v2.1	256GB	256Gb*8	TLC	M-die	KLUEG8U1EM-B0C10**	890/260	48K / 42K		
	(Gear 3 x	(Gear 3 x 128GB 128Gb*8	E-die	KLUDG8V1EE-B0C10**	880/230	40K / 33K	11.5 x 13.0 x 1.0	CS		
High-End	2 lanes)	64GB	128Gb*4	MLC	D-die	KLUCG4J1ED-B0C10**	880/200	48K / 35K		
	UFS v2.0 (Gear 3 x 256GB 2 lanes)	256GB	256Gb*8	TLC	M-die	KLUEG8U1EM-B0B10**	850/260	45K / 40K	11.5 x 13.0 x 1.2	MP
	UFS 2.0	128GB	128Gb*8		B-die	KLUDG8J1CB-B0B10**			11.5 x 13.0 x 1.2	
	(Gear 3 x	64GB	128Gb*4	MLC		KLUCG4J1CB-B0B10**	460/160	20K / 14K		MP
	1 lane)	32GB	64Gb*4		E-die	KLUBG4G1CE-B0B10**				
		256GB	256Gb*8	TLC	M-die	KLMEG8UERM-C0410**			11.5 x 13.0 x 1.0	CS
Mainstream		128GB	256Gb*4	ILU	ivi-die	KLMDG4UERM-B0410**				
	eMMC v5.1	64GB	128Gb*4			KLMCG4JETD-B0410**	200/150	001/ / 101/		
	(Gear 3 x 1 lane)	32GB	128Gb*2	MLC	D-die	KLMBG2JETD-B0410**	320/150	22K / 18K		CS in Dec / Jan
		16GB	128Gb*1	MLC		KLMAG1JETD-B0410**			11.5 x 13.0 x 0.8	2007 ball
		8GB	64Gb*1		F-die	KLM8G1GETF-B0410**				

MMC5.1 is backwards compatible with 5.0 & 4.5

<sup>\*</sup>Denotes bucket code for latest firmware patch

## eMCP: eMMC + LPDDR3

Memory	eMMC Density	DRAM Density/Organization	Voltage (eMMC-DRAM)	Package
	8GB	8Gb (x32)	3.3V/1.8V - 1.8V/1.2V	221FBGA 11.5 x 13mm
		8Gb (x32)		
	16GB	8Gb*2 (x32)	3.3V/1.8V - 1.8V/1.2V	221FBGA 11.5 x 13mm
		6Gb*4 (x32)		
		8Gb*2 (x32)		
eMMC & MDRAM	32GB	6Gb*4 (x32)	3.3V/1.8V - 1.8V/1.2V	221FBGA 11.5 x 13mm
		8Gb*4 (x32)		
	0.400	6Gb*4 (x32)	0.07/4.07/ 4.07/4.07/	004FDCA 11 F v 10mm
	64GB	8Gb*4 (x32)	3.3V/1.8V - 1.8V/1.2V	221FBGA 11.5 x 13mm
	128GB	8Gb*4 (x32)	3.3V/1.8V - 1.8V/1.2V	221FBGA 11.5 x 13mm

## eMCP: eMMC + LPDDR4X

Memory	eMMC Density	DRAM Density/Organization	Voltage (eMMC-DRAM)	Package
	22CP	12Gb*2 (x32)	3.3V/1.8V - 1.8V/1.2V/0.6V	254FBGA 11.5 x 13mm
	32GB	8Gb*4 (x32)	3.37/1.07 - 1.07/1.27/0.07	ZOAFDUA II.O X TOIIIIII
eMMC & MDRAM		12Gb*2 (x32)		
EIVIIVIC & IVIDRAIVI	64GB	8Gb*4 (x32)	3.3V/1.8V - 1.8V/1.2V/0.6V	254FBGA 11.5 x 13mm
		12Gb*4 (x32)		
	128GB	12Gb*4 (x32)	3.3V/1.8V - 1.8V/1.2V/0.6V	254FBGA 12 x 15mm

## ePoP: eMMC + LPDDR3

Memory	eMMC Density	DRAM Density/Organization	Voltage (eMMC-DRAM)	Package
	4GB	4Gb (x32)	3.3V/1.8V - 1.8V/1.2V	168FBGA 12x12mm
	400	6Gb (x32)	3.3V/1.0V - 1.0V/1.2V	TOOFDUA TZXTZIIIII
eMMC & MDRAM	40D	4Gb (x32)	0.01//4.01/4.01//4.01/	1.20FDCA 1.0vd.0mm
	4GB	6Gb (x32)	3.3V/1.8V - 1.8V/1.2V	136FBGA 10x10mm
	8GB	8Gb (x32)	3.3V/1.8V - 1.8V/1.2V	136FBGA 10x10mm

## Solid State Drives (SSDs)

		Server & Clou	ud Datacenter		Enterprise	
		LEGACY SERVERS	HIGH-DENSITY SERVERS	ALL FLASH PRIMARY STORAGE Hard Disk Drive Replacement	LOW LATENCY PRIMARY STORAGE Next-Generation All Flash Array	EXTREME PERFORMANCE SERIES Server-side Caching
		PM863a	PM963	PM1633a	PM1725a	PM1725a
	Host Interface	SATA 3.0 @ 6 Gbit/s	PCIe Gen 3 x4 @ 32Gbit/s (NVMe)	SAS 3.0 @ 12 Gbit/s	PCIe Gen 3 x4 @ 32Gbit/s (NVMe)	PCIe Gen 3 x8 @ 64Gbit/s (NVMe)
	Form Factor	2.5"	M.2 (22x110mm)	2.5"	2.5" / U.2	Add-in Card (HHHL)
	Capacity (GB)	240/480/960/ 1920/3840	960/1920	480/960/1920/ 3840/7680/15360	3840/7680/15360	1600/3200/6400
En	durance (up to)	1.3 DWPD for 3 Years	1.3 DWPD for 3 Years	1-3 DWPD for 5 Years	5 DWPD for 5 Years	5 DWPD for 5 Years
Power Consu	mption (Active)	4 W	7.5 W	13 W	25 W	23 W
Power Con	sumption (Idle)	1.3 W	2.5 W	7 W	7 W	7.7 W
Rando	m Reads (up to)	99,000 IOPS	430,000 IOPS	205,000 IOPS	740,000 IOPS	1,080,000 IOPS
Randor	m Writes (up to)	18,000 IOPS	40,000 IOPS	39,000 IOPS	70,000 IOPS	170,000 IOPS
Sequenti	al Reads (up to)	520 MB/s	2,000 MB/s	1,300 MB/s	3,100 MB/s	6,400 MB/s
Sequentia	al Writes (up to)	480 MB/s	1,800 MB/s	1,400 MB/s	3,000 MB/s	3,000 MB/s
	MTBF	2.0 Million Hours	2.0 Million Hours	2.0 Million Hours	2.0 Million Hours	2.0 Million Hours
Uncorrectabl	le Bit Error Rate (UBER)	1 in 10 <sup>17</sup>	1 in 10 <sup>17</sup>	1 in 10 <sup>17</sup>	1 in 10 <sup>17</sup>	1 in 10 <sup>17</sup>
Physi	cal Dimensions	100 x 70 x 7mm	22 x 110 x 4.15 mm	100 x 70 x 15 mm	100 x 70 x 15 mm	168 x 70 x 19 mm (HHHL)
	Weight	55 g	20 g	160 g	160 g	330 g

## **SOLID STATE DRIVES (SSD)**

Drive Type	Power-loss Protection	Form Factor	Interface	Connector	Product Family	Write Endurance	Capacity (GB)	Part Number
							256	MZNLN256HMHQ-00000
			SATA 3.0 @ 6 Gbit/s		PM871a		512	MZNLN512HMJP-00000
Client PC/	No	M.2 22 x 80 mm		M.2		PC Workload	1024	MZNLN1T0HMLH-00000
Embedded	INU	IVI.Z ZZ X OU IIIIII		IVI.Z		PG WOIKIOAU	128	MZVLV128HCGR-00000
			PCle Gen 3 x4 @ 32Gbit/s (NVMe)		PM951		256	MZVLV256HCHP-00000
							512	MZVLV512HCJH-00000
							240	MZ7LM240HMHQ-00005
							480	MZ7LM480HMHQ-00005
					PM863a	0.8 DWPD for 5 Years	960	MZ7LM960HMJP-00005
						101 0 10010	1920	MZ7LM1T9HMJP-00005
							3840	MZ7LM3T8HMLP-00005
							120	MZ7KM120HAFD-00005
							240	MZ7KM240HAGR-00005
			SATA 3.0 @ 6 Gbit/s	SFF-8223		3.6 DWPD for 5 Years	480	MZ7KM480HAHP-00005
						101 0 10010	960	MZ7KM960HAHP-00005
					OMOGO		1920	MZ7KM1T9HAJM-00005
					SM863		100	MZ7KM120HAFD-00005
							200	MZ7KM240HAGR-00005
		2.5" 7mmT				10 DWPD for 5 Years	400	MZ7KM480HAHP-00005
							101 0 10013	800
							1600	MZ7KM1T9HAJM-00005
	V					0.8 DWPD	480	MZQLW480HMHQ-00003
atacenter	Yes						960	MZQLW960HMJP-00003
					PM963	for 5 Years	1920	MZQLW1T9HMJP-00003
							3840	MZQLW3T8HMLP-00003
							960	MZQKW960HMJP-00003
				U.2 (SFF-8639)		3.6 DWPD for 5 Years	1920	MZQKW1T9HMJP-00003
						IOI 5 IGAIS	3840	MZQKW3T8HMLH-00003
					SM963		800	MZQKW960HMJP-00003
			PCle Gen 3x4 @ 32Gbit/s (NVMe)			10 DWPD for 5 Years	1600	MZQKW1T9HMJP-00003
			SZGDIVS (NVIVIE)			IUI J IEAIS	3200	MZQKW3T8HMLH-00003
							480	MZ1LW480HMHQ-00003
					PM963	0.8 DWPD	960	MZ1LW960HMJP-00003
						for 5 Years	1920	MZ1LW1T9HMLS-00003
		M.2 22 x 110 mm		M.2		3.6 DWPD	960	MZ1KW960HMJP-00003
						for 5 Years	1920	MZ1KW1T9HMJP-00003
					SM963	10 DWPD	800	MZ1KW960HMJP-00003
						for 5 Years	1600	MZ1KW1T9HMJP-00003

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## **SOLID STATE DRIVES (SSD)** continued

Drive Type	Power-loss Protection	Form Factor	Interface	Connector	Product Family	Write Endurance	Capacity (GB)	Part Number
							480	MZILS480HCGR-00003
					1 DWPD	960	MZILS960HCHP-00003	
					for 5 Years	1920	MZILS1T9HCHP-00003	
				PM1633		3840	MZILS3T8HCJM-00003	
				PIVITOSS		400	MZILS480HCGR-00003	
						3 DWPD for 5 Years	800	MZILS960HCHP-00003
			SAS 3.0 @ 12 Gbit/s	SFF-8680			1600	MZILS1T9HCHP-00003
	2.5" 15mmT	SAS 3.0 @ 12 GDIVS	311-0000			3200	MZILS3T8HCJM-00003	
						480	MZILS480HEGR-00007	
		2.0 (3)			PM1633a		960	MZILS960HEHP-00007
Enterprise	Yes					1 DWPD for 5 Years	1920	MZILS1T9HEJH-00007
							3840	MZILS3T8HMLH-00007
							7680	MZILS7T6HMLS-00007
							15360	MZILS15THMLS-00007
							800	MZWLL800HEHP-00003
			PCle Gen 3x4 @	U.2 (SFF-8639)			1600	MZWLL1T6HEHP-00003
			32Gbit/s (NVMe)	0.2 (3FF-0039)			3200	MZWLL3T2HMJP-00003
					PM1725a	5 DWPD for 5 Years	6400	MZWLL6T4HMLS-00003
						0 700.0	1600	MZPLL1T6HEHP-00003
		Add-in Card (HHHL)	PCle Gen 3 x8 @ 64Gbit/s (NVMe)	Edge Connector			3200	MZPLL3T2HMJP-00003
	O4GDIVS (INVINE)			6400	MZPLL6T4HMLT-00003			

## Public Information Display (PID) Product Classification

Super Narrow Bezel (SNB)/ Ultra Narrow Bezel (UNB)		» SNB: 5.9mm A-to-A	» UNB: 3.9mm A-to-A
Indoor PID	Name Paral	» 40"/46"/55"/75"	» 700 nits Brightness
E-Board PID	» Landscape Orientation	» 55"/70"/82" Edge LED	» AGAR Surface Treatment
Outdoor PID	» High Brightness	» Full High Definition	» 110°C Clearing Point

## Why PID instead of TV?

	COMMERCIAL (PID)	CONSUMER (TV)
WARRANTY	18 months to 2 years	90 days to 1 year
RELIABILITY	Public environments 20+ hours daily duty cycle Variety of temperatures & location	5-8 hour daily duty cycle Designed for in-home use in controlled environment In-home living room
PRODUCTION LIFECYCLE	24-36 months	12-15 months
PICTURE QUALITY	Designed to resist image retention  LCD backlight covers a wider color spectrum necessary for PC source integration, giving better picture quality  AGAR coating for public viewing	120Hz / 240Hz for full-motion video Designed for TV signals Gloss surface treatment
LOCATION	Most models portrait capable	Can only be oriented in landscape mode

## **Product Segmentation**

HEAVY US	E			
Ī	SNB/UNB	Professional	Indoor Events	Billboard
		Control Room     Simulation	<ul><li>Scoreboard</li><li>Sports Broadcasting</li></ul>	Dynamic Signage
	Indoor PID	Entertainment	Transportation	Communication
		<ul><li>Casino</li><li>Theatre</li><li>Menu</li></ul>	<ul><li>Airport</li><li>Train/Bus Station</li></ul>	Conference Room
	E-Board PID	Commercial	Education	Hospitality
		<ul><li>Kiosk</li><li>Conference Systems</li></ul>	Interactive FPD	Hotel Signage
	Outdoor PID	Commercial	Education	Hospitality
LIGHT USI	E	<ul><li>Kiosk</li><li>Conference Systems</li></ul>	Interactive FPD	Hotel Signage

## **Product Segmentation**

Туре	Class	Warranty	Bezel	Suggested Run Time	Brightness	Usage	Applications	Value Tier
ENB / UNB / SNB	Ultra / Super Narrow Bezel	2 years	1.9mm - 5.9mm A-to-A	20+ hours	500-700 nits	Heavy	Video Walls	Premium commercial range
Indoor PID	Indoor Commercial Panels	2 years	Narrow	20+ hours	600/700 nits	Medium	Semi-Outdoor	Mid-price range
E-Board	Value, Large Format	18 months	Normal	12 hours	450 nits	Daily	Indoor, e-Board	High-value commercial range
Outdoor PID	High Bright, Wide Temp	2 years	Normal	20+ hours	2500-5000 nits	Heavy	Outdoor	Premium commercial range
Specialty	Value, Large Format	2 years	Narrow	20+ hours	500/ 1500 nits	Medium	specialty	

## SAMSUNG DIGITAL INFORMATION DISPLAY (DID) PANEL LINEUP

Category	Model	Size	Model Resolution	Bezel	Backlight	Brightness (typical)	Contrast Ratio	Response Time	Frequency	MP*	Comment		
	LTI460HN09-0			Super narrow		500 nits					5.9mm Active to Active, LED		
	LTI460HN11-A			Ultra narrow		500 nits				Now	3.9mm Active to Active, LED		
SNB /	LTI460HN12-V	46"		Oltra Harrow		700 nits					3.9mm Active to Active, LLD		
UNB / ENB	LTI460HN13-V		FHD	Extreme	D-LED	700 nits	3,000:1	8ms	60Hz	Feb., '17	2.0mm Active to Active, LED		
LND	LTI460HN14-V			narrow		500 nits				Q2, '17			
	LTI550HN11-V	55"		Ultra narrow		500 nits				Now	3.9mm Active to Active, LED		
	LTI550HN12-V	00		Ultra harrow		700 nits				INOW	3.311111 Active to Active, LLD		
	LTI550HN13-V (Broadcast)				D-LED	700 nits							
	LTI550HN14-V	55"			55"		3,000:1		60Hz				3.9mm Active to Active, LED
	LTI550HN17-V				55	55"							
	LTI460HN08	46"	FHD		eLED	700 nits				Now			
	LTI480HN01-0	48"		Ultra narrow	Slim eLED	70011113					Slim eLED,Landscape / Portrait		
	LTI480HN02-0	40			SIIIII ELLD	500 nits	4,000:1				omin occo,canassaps / i situat		
Indoor PID	LTI550HN06				eLED	700 nits	4,000.1	8ms			eLED, Landscape / Portrait		
	LTI550HN07-0	55"			CLLD	450 nits					E-Board; Landscape/Portrait		
	LTI550FN01-N		UHD		Slim eLED	500 nits		120			Slim eLED, Landscape / Portrait		
	LTI750HF02-0		FHD		D-LED	400 nits	3,500:1		120Hz	120Hz	Landscape / Portrait		
	LTI750FJ01-N	75"		Normal	5 225	500 nits	5,000:1				Landsaps / Fordale		
	LTI750FN01-V		UHD	eLED	600 nits	4.000.1	COLL	16. Q2	al ED Landagana / Dortrait				
	LTI980FN01-V	98"			eren	500 nits	4,000:1		60Hz	Jan., '17	eLED Landscape / Portrait		
	LTI550HN15-0	55"		Narrow	eLED	380 nits					Value PID		
E-Board	LTI700HA02-0	70"	FHD		GLLD	350 nits	4,000:1	8ms	60Hz	Now	E-Board; Landscape mode only		
L Dourd	LTI750HF02-0	75"	1110	Normal	D-LED	450 nits	1,000.1	Onio	OOTIE	14044			
	LTI750FN02-N	7.5			eLED	350 nits					E-Board; Landscape mode only		
	LTI460HZ01-V	46"				5,000 nits	4,000:1		60Hz				
Outdown	LTI460HF01-V	10	FUD	Name	חודה	0.500 - 4-		0		Maria	High Dright Hi Tagan LO 4/4) Dal		
Outdoor	LTH550HF04- V(A)	55"	FHD	Narrow	D-LED	2,500 nits	3,000:1	8ms	120Hz	Now	High Bright, Hi Temp LC, 1/4λ Pol.		
	LTI750HF01-V	75"				3,500 nits							
	LTI290LN01-0	29"				500 nits					Stretched, 40"/2, Hi Temp LC		
Specialty	LTI290LN02-0	23	Half FHD	Narrow	eLED	700 nits	4.000:4	16ms	60Hz	Now	Su etcheu, 40 72, Hi Temp LC		
орестану	LTI370LN03-V	37"	ΠαΠΤΙΙΟ	Nallow	ULLD	7 00 11113	4,000:1				Stretched, 46"/2, Hi Temp LC		
	LTI370LN02-V	J1				1500 nits				Q1, '17	onotolicu, 40 /2, III Icilip Lo		

## Contacts

Feel free to contact your local distributor or sales representative with any Samsung sales inquiries.

#### Adelsa | www.adetronics.com.mx

PRODUCTS	ADDRESS		MAIN PHONE	FAX
Memory, SLSI, LCD	MEXICO	Hacienda Corralejo #80, Bosque de Echegaray, Naucalpan, Mexico 53310	52-555-560-5002	
	GUADALAJARA OFFICE		52-333-122-3054	
	MONTERREY OFFICE		52-818-214-0011	
	CD. JUAREZ OFFICE		52-656-613-3517	
	REYNOSA OFFICE		52-899-922-5540	

## ATMI Sales | www.atmisales.com

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	WASHINGTON	8581 154th Avenue NE Redmond WA 98052	425-869-7636	425-869-9841

## Bear VAI Technology | www.bearvai.com

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	MAIN OFFICE - INDIANA	11451 Overlook Drive Fishers, IN 46037	440-832-7637	317-845-8650
MICHIGAN		5506 Alpine Ridge Stevensville, MI 49127	440-526-1991	440-526-5426

## Crestone Technology Group | www.crestonegroup.com

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Memory, SLSI, LCD	COLORADO	7108 S. Alton Way, Building L, Suite A Centennial, CO 80112	303-280-7202	720-482-2220
	UTAH		801-973-8909	

## Customer 1st | www.customer1st.com

PRODUCTS	ADDRESS		MAIN PHONE	FAX
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	KANSAS	2111 E. Crossroad Lane, #202 Olathe, KS 66062		

 $\boldsymbol{\rightarrow} \text{ For all product information please visit: } \mathbf{www.samsung.com/us/samsungsemiconductor}$ 

## InTELaTECH | www.intelatech.com

PRODUCTS	ADDRESS	MAIN PHONE	FAX
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	5225 Orbitor Drive, Mississauga, Ont, Canada L4W 4Y8	905-629-0082	905-624-6909

## I-Squared Incorporated | www.isquared.com

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	1250 B Street, Petaluma, CA 94952	707-773-3108	

## IRI Rep | www.irirep.com

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## IRI WEST | www.iriwest.com

PRODUCTS	ADDRESS		MAIN PHONE	FAX
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	DALLAS	2745 Dallas Pkwy, Suite 460 Plano, TX 75093	972-680-2800	972-699-0330
	HOUSTON	24624 Interstate 45 North, Suite 200 Spring, TX 77386	832-940-9600	512-343-1922

## Neptune Electronics (necco) | www.neccoelect.com

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## **New Tech Solutions**

PRODUCTS	ADDRESS	MAIN PHONE	FAX
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## Rep One Associates, Inc. | www.repone.com

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	FLORIDA		704 516-0242	
	GEORGIA	3000 Langford Road, Building 300 Norcross, GA 30071	770-209-9242 678-591-6753	770-209-9245
	NORTH & SOUTH CAROLINA	912 Oleander Lane Waxhaw, NC 28173	704 516-0242	

## Tech Coast Sales | www.tc-sales.com

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Notes		



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